

SOT-23-3L Plastic-Encapsulate MOSFETS

**AO3423A** P-Channel 20-V(D-S) MOSFET

V(BR)DSS	RDS(on)MAX	ID
-20 V	120mΩ@-4.5V	-2A
	150mΩ@-2.5V	

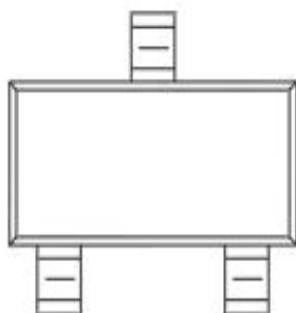
**FEATURE**

- ※ TrenchFET Power MOSFET
- ※ ESD Protected 2.0KV

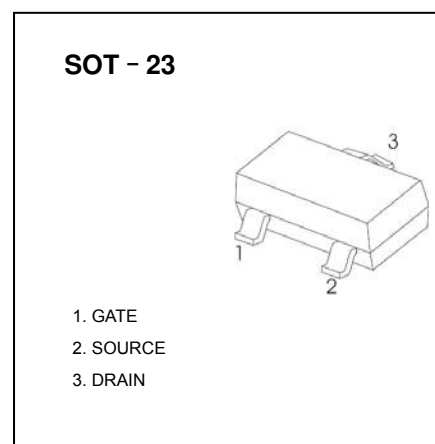
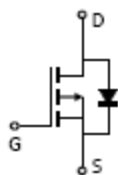
**APPLICATION**

- ※ Load Switch for Portable Devices
- ※ DC/DC Converter

**MARKING**



**Equivalent Circuit**



**Maximum ratings ( Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	-20	V
Gate-Source Voltage	VGS	±12	
Continuous Drain Current	ID	-2	A
Pulsed Diode Curren	IDM	-18	
Power Dissipation	PD	1.4	W
Thermal Resistance from Junction to Ambient (t≤5s)	RθJA	125	°C/W
Operating Junction	TJ	150	°C
Storage Temperature	TSTG	-55~+150	

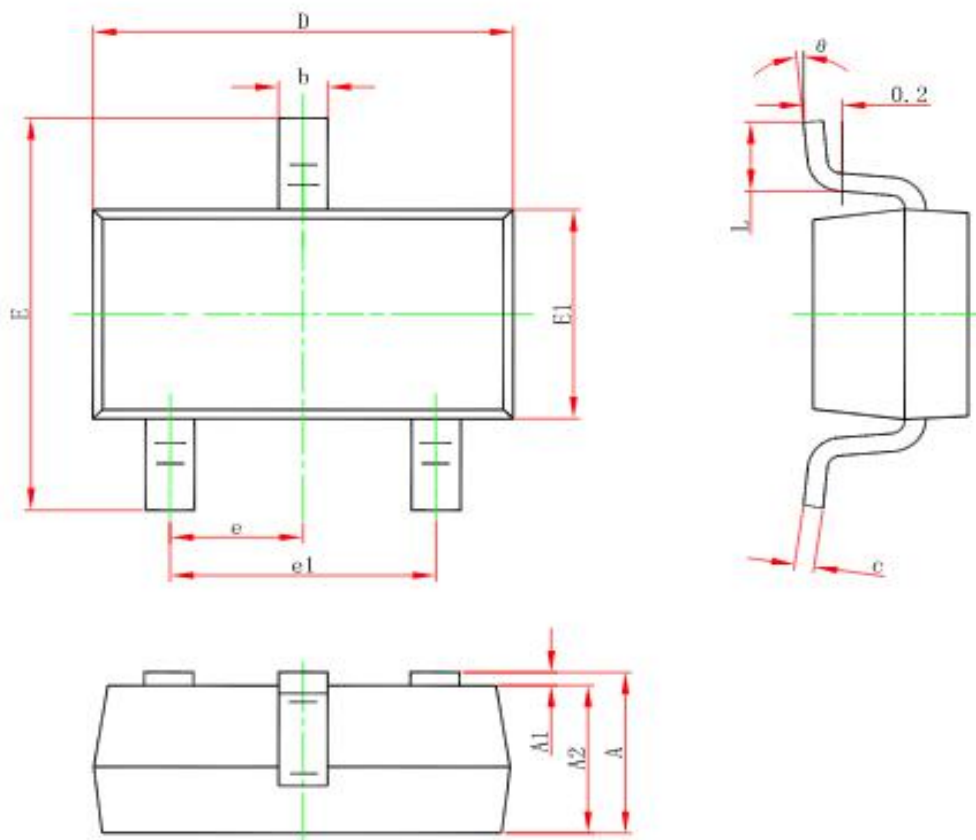
**SOT-23-3L Plastic-Encapsulate MOSFETS**
**MOSFET ELECTRICAL CHARACTERISTICS**
**Static Electrical Characteristics (Ta = 25 °C Unless Otherwise Noted)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = -250μA	-20			V
Gate-source threshold voltage	VGS(th)	VDS = VGS, ID = -250μA	-0.4		-1	V
Gate-source leakage	IGSS	VDS = 0V, VGS = ±12V			±10	μA
Zero gate voltage drain current	IDSS	VDS = -20V, VGS = 0V			-1	μA
Drain-source on-state resistancea	RDS(on)	VGS = -4.5V, ID = -2.5A		59	120	mΩ
		VGS = -2.5V, ID = -2A		72	150	mΩ
Forward transconductancea	gfs	VDS = -4.5V, ID = -2.5A		7		S
Diode forward voltage	VSD	IS = -1A, VGS = 0V		-0.8	-1.2	V
<b>Dynamic</b>						
Input capacitance	Ciss	VDS = -4.5V, VGS = 0V, f = 1MHz		325		pF
Output capacitance	Coss			63		pF
Reverse transfer capacitanceb	Crss			37		pF
Total gate charge	Qg	VDS = -10V, VGS = -4.5V, ID = -2A		3.2		nC
Gate-source charge	Qgs			0.6		nC
Gate-drain charge	Qgd			0.9		nC
Gate resistance	Rg	f = 1MHz		11.2		Ω
<b>Switchingb</b>						
Turn-on delay time	td(on)	VDD = -10V RL = 3Ω, ID ≈ -1A, VGEN = -4.5V, Rg = 3Ω		11		ns
Rise time	tr			5.5		ns
Turn-off delay time	td(off)			22		ns
Fall time	tf			8		ns
Body Diode Reverse Recovery Time	trr	If = -2A, dI/dt = 100A/us				ns
Body Diode Reverse Recovery Charge	grr	If = -2A, dI/dt = 100A/us				nC

**Note :**

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t < 5 sec.
3. Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.

SOT-23-3L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°